

Integrated Relay, Inductive Load Driver

NUD3105

This device is used to switch inductive loads such as relays, solenoids incandescent lamps, and small DC motors without the need of a free-wheeling diode. The device integrates all necessary items such as the MOSFET switch, ESD protection, and Zener clamps. It accepts logic level inputs thus allowing it to be driven by a large variety of devices including logic gates, inverters, and microcontrollers.

Features

- Provides a Robust Driver Interface Between DC Relay Coil and Sensitive Logic Circuits
- Optimized to Switch Relays from 3.0 V to 5.0 V Rail
- Capable of Driving Relay Coils Rated up to 2.5 W at 5.0 V
- Internal Zener Eliminates the Need of Free-Wheeling Diode
- Internal Zener Clamp Routes Induced Current to Ground for Quieter Systems Operation
- Low V_{DS(on)} Reduces System Current Drain
- SZ Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free and Halide Free

Typical Applications

- Telecom: Line Cards, Modems, Answering Machines, FAX
- Computers and Office: Photocopiers, Printers, Desktop Computers
- Consumer: TVs and VCRs, Stereo Receivers, CD Players, Cassette Recorders
- Industrial:Small Appliances, Security Systems, Automated Test Equipment, Garage Door Openers
- Automotive: 5.0 V Driven Relays, Motor Controls, Power Latches, Lamp Drivers

RELAY/INDUCTIVE LOAD DRIVER 0.5 AMPERE, 8.0 VOLT CLAMP





SOT-23 (TO-236) CASE 318 SC-74 CASE 318F STYLE 7

MARKING DIAGRAMS





JW4 = Device Code
M = Date Code*
D = Date Code
= Pb-Free Package

(Note: Microdot may be in either location)
*Date Code orientation and/or overbar may
vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping [†]
NUD3105LT1G	SOT-23 (Pb-Free)	3000 / Tape & Reel
NUD3105DMT1G	SOT-74 (Pb-Free)	3000 / Tape & Reel
SZNUD3105DMT1G	SOT-74 (Pb-Free)	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

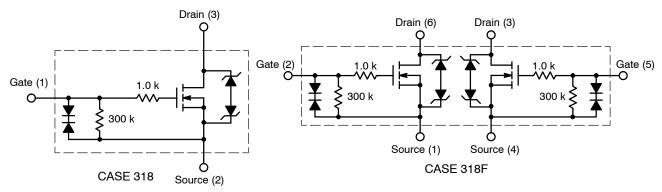


Figure 1. Internal Circuit Diagrams

MAXIMUM RATINGS (T_J = 25°C unless otherwise specified)

Symbol	Rating	Value	Unit	
V_{DSS}	Drain to Source Voltage - Continuous		6.0	V _{dc}
V _{GS}	Gate to Source Voltage – Continuous		6.0	V _{dc}
I _D	Drain Current – Continuous		500	mA
Ez	Single Pulse Drain-to-Source Avalanche Energy (T	J _{initial} = 25°C) (Note 2)	50	mJ
E _{zpk}	Repetitive Pulse Zener Energy Limit (DC ≤ 0.01%)	4.5	mJ	
T_J	Junction Temperature	150	°C	
T _A	Operating Ambient Temperature	-40 to 85	°C	
T _{stg}	Storage Temperature Range		-65 to +150	°C
P_{D}	Total Power Dissipation (Note 1) Derating Above 25°C	SOT-23	225 1.8	mW mW/°C
	Total Power Dissipation (Note 1) Derating Above 25°C	SC-74	380 1.5	mW mW/°C
$R_{ hetaJA}$	Thermal Resistance, Junction-to-Ambient	SOT-23 SC-74	556 329	°C/W

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality

ELECTRICAL CHARACTERISTICS (T_{.J} = 25°C unless otherwise noted)

Symbol	Characteristic	Min	Тур	Max	Unit			
OFF CHARAC	FF CHARACTERISTICS							
V_{BRDSS}	Drain to Source Sustaining Voltage (Internally Clamped), (I _D = 10 mA)	6.0	8.0	9.0	V			
B _{VGSO}	I _g = 1.0 mA	-	-	8.0	V			
I _{DSS}	Drain to Source Leakage Current $(V_{DS} = 5.5 \text{ V}, V_{GS} = 0 \text{ V}, T_J = 25^{\circ}\text{C})$ $(V_{DS} = 5.5 \text{ V}, V_{GS} = 0 \text{ V}, T_J = 85^{\circ}\text{C})$	- -	- -	15 15	μΑ			
I _{GSS}	Gate Body Leakage Current (318) (V _{GS} = 3.0 V, V _{DS} = 0 V) (V _{GS} = 5.0 V, V _{DS} = 0 V)	5.0 -	- -	19 50	μΑ			
	Gate Body Leakage Current (318F) (V _{GS} = 3.0 V, V _{DS} = 0 V) (V _{GS} = 5.0 V, V _{DS} = 0 V)	5.0 -	- -	35 65	μΑ			

should not be assumed, damage may occur and reliability may be affected.

1. This device contains ESD protection and exceeds the following tests:

Human Body Model 2000 V per MIL_STD-883, Method 3015.

Machine Model Method 200 V.

2. Refer to the section covering Avalanche and Energy.

$\textbf{ELECTRICAL CHARACTERISTICS} \ (T_J = 25^{\circ}C \ unless \ otherwise \ noted) \ (continued)$

Symbol	Characteristic	Min	Тур	Max	Unit
ON CHARAC	TERISTICS	•			•
V _{GS(th)}	Gate Threshold Voltage $ (V_{GS} = V_{DS}, I_D = 1.0 \text{ mA}) $ $ (V_{GS} = V_{DS}, I_D = 1.0 \text{ mA}, T_J = 85^{\circ}\text{C}) $	0.8 0.8	1.2	1.4 1.4	V
R _{DS(on)}	Drain to Source On–Resistance $ \begin{array}{l} (I_D=250 \text{ mA, V}_{GS}=3.0 \text{ V}) \\ (I_D=500 \text{ mA, V}_{GS}=3.0 \text{ V}) \\ (I_D=500 \text{ mA, V}_{GS}=5.0 \text{ V}) \\ (I_D=500 \text{ mA, V}_{GS}=5.0 \text{ V}) \\ (I_D=500 \text{ mA, V}_{GS}=3.0 \text{ V, T}_{J}=85^{\circ}\text{C}) \\ (I_D=500 \text{ mA, V}_{GS}=5.0 \text{ V, T}_{J}=85^{\circ}\text{C}) \end{array} $	- - - -	- - - -	1.2 1.3 0.9 1.3 0.9	Ω
I _{DS(on)}	Output Continuous Current $(V_{DS} = 0.25 \text{ V}, V_{GS} = 3.0 \text{ V})$ $(V_{DS} = 0.25 \text{ V}, V_{GS} = 3.0 \text{ V}, T_J = 85^{\circ}\text{C})$	300 200	400 -	-	mA
9FS	Forward Transconductance (V _{OUT} = 5.0 V, I _{OUT} = 0.25 A)	350	570	-	mmhos
YNAMIC CH	ARACTERISTICS	-			-
C _{iss}	Input Capacitance (V _{DS} = 5.0 V,V _{GS} = 0 V, f = 10 kHz)	-	25	-	pF
C _{oss}	Output Capacitance (V _{DS} = 5.0 V, V _{GS} = 0 V, f = 10 kHz)	-	37	-	pF
C _{rss}	Transfer Capacitance $(V_{DS} = 5.0 \text{ V}, V_{GS} = 0 \text{ V}, f = 10 \text{ kHz})$	-	8.0	_	pF
WITCHING (CHARACTERISTICS	-			
t _{PHL} t _{PLH}	Propagation Delay Times: High to Low Propagation Delay; Figure 1 (5.0 V) Low to High Propagation Delay; Figure 1 (5.0 V)		25 80	_ _	nS
t _{PHL} t _{PLH}	High to Low Propagation Delay; Figure 1 (3.0 V) Low to High Propagation Delay; Figure 1 (3.0 V)	-	44 44	- -	
t _f tr	Transition Times: Fall Time; Figure 1 (5.0 V) Rise Time; Figure 1 (5.0 V)	- -	23 32	- -	nS
t _f t _r	Fall Time; Figure 1 (3.0 V) Rise Time; Figure 1 (3.0 V)	-	53 30		

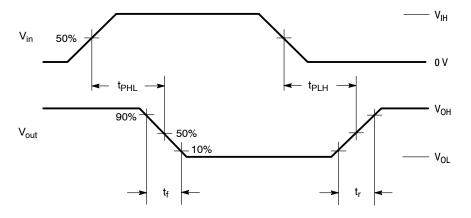


Figure 1. Switching Waveforms

TYPICAL CHARACTERISTICS

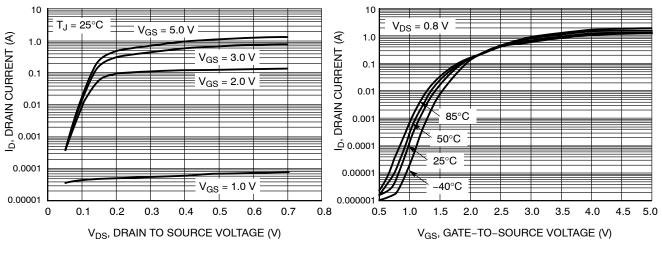


Figure 2. Output Characteristics

Figure 3. Transfer Function

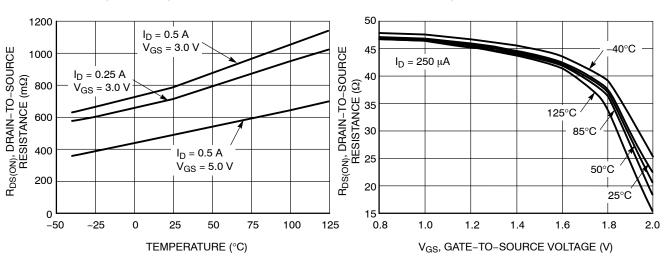


Figure 4. On Resistance Variation vs. Temperature

Figure 5. R_{DS(ON)} Variation with Gate-To-Source Voltage

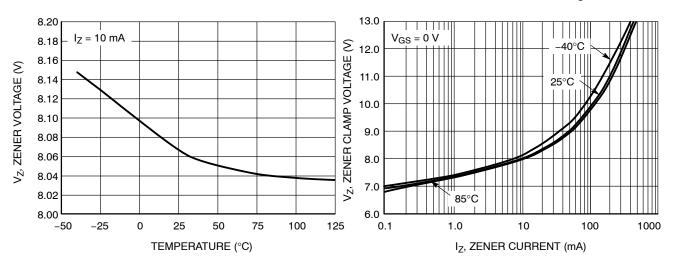


Figure 6. Zener Voltage vs. Temperature

Figure 7. Zener Clamp Voltage vs. Zener Current

TYPICAL CHARACTERISTICS (continued)

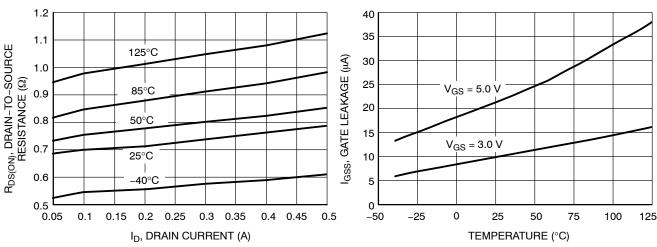


Figure 8. On–Resistance vs. Drain Current and Temperature

Figure 9. Gate Leakage vs. Temperature

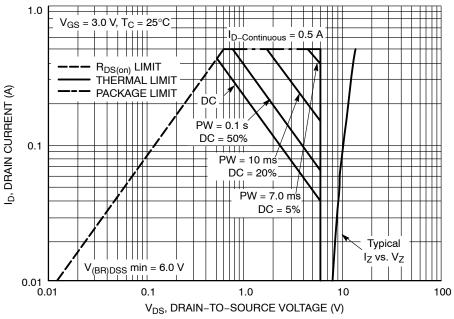


Figure 10. Safe Operating Area

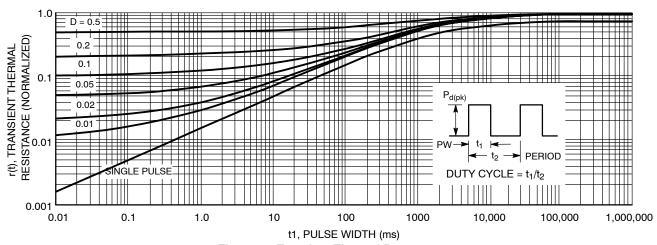


Figure 11. Transient Thermal Response

Designing with this Data Sheet

- 1. Determine the maximum inductive load current (at max V_{CC} , min coil resistance & usually minimum temperature) that the NUD3105 will have to drive and make sure it is less than the max rated current.
- 2. For pulsed operation, use the Transient Thermal Response of Figure 11 and the instructions with it to determine the maximum limit on transistor power dissipation for the desired duty cycle and temperature range.
- 3. Use Figures 10 and 11 with the SOA notes to insure that instantaneous operation does not push the device beyond the limits of the SOA plot.

- Verify that the circuit driving the gate will meet the V_{GS(th)} from the Electrical Characteristics table
- 5. Using the max output current calculated in step 1, check Figure 7 to insure that the range of Zener clamp voltage over temperature will satisfy all system & EMI requirements.
- 6. Use I_{GSS} and I_{DSS} from the Electrical Characteristics table to ensure that "OFF" state leakage over temperature and voltage extremes does not violate any system requirements.
- 7. Review circuit operation and insure none of the device max ratings are being exceeded.

APPLICATIONS DIAGRAMS

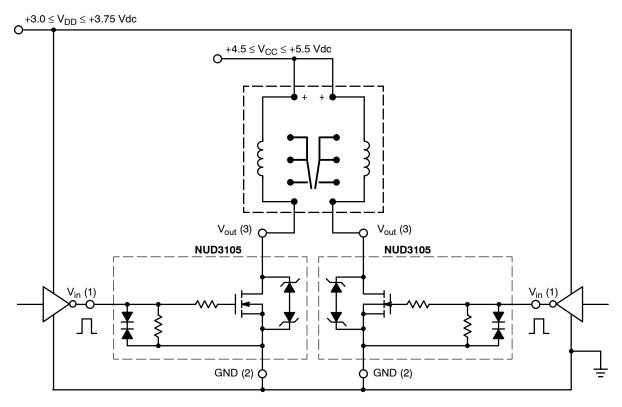


Figure 12. A 200 mW, 5.0 V Dual Coil Latching Relay Application with 3.0 V Level Translating Interface

Max Continuous Current Calculation

for TX2–5V Relay, R1 = 178 Ω Nominal @ R_A = 25°C Assuming \pm 10% Make Tolerance, R1 = 178 Ω * 0.9 = 160 Ω Min @ T_A = 25°C T_C for Annealed Copper Wire is 0.4%/°C R1 = 160 Ω * [1+(0.004) * (-40°-25°)] = 118 Ω Min @ -40°C I_O Max = (5.5 V Max – 0.25V) /118 Ω = 45 mA

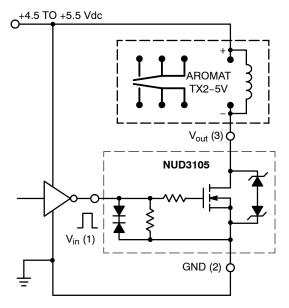


Figure 13. A 140 mW, 5.0 V Relay with TTL Interface

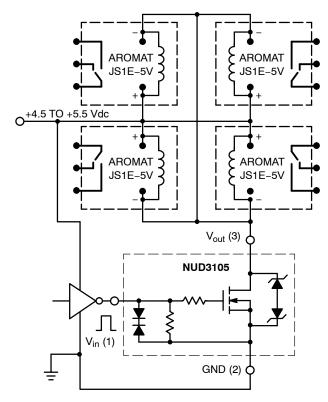


Figure 14. A Quad 5.0 V, 360 mW Coil Relay Bank



SOT-23 (TO-236) CASE 318-08 **ISSUE AS**

DATE 30 JAN 2018

SCALE 4:1 D - 3X b

TOP VIEW







RECOMMENDED SOLDERING FOOTPRINT



DIMENSIONS: MILLIMETERS

3. ANODE

NOTES:

- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
 2. CONTROLLING DIMENSION: MILLIMETERS.
 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH.
 MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL
- 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	MILLIMETERS				INCHES	
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
С	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
е	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
HE	2.10	2.40	2.64	0.083	0.094	0.104
Т	O٥		100	O٥		10°

GENERIC MARKING DIAGRAM*



XXX = Specific Device Code

= Date Code

= Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

STYLE 1 THRU 5: CANCELLED	STYLE 6: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 7: PIN 1. EMITTER 2. BASE 3. COLLECTOR	STYLE 8: PIN 1. ANODE 2. NO CONNECTION 3. CATHODE		
STYLE 9:	STYLE 10:	STYLE 11:	STYLE 12:	STYLE 13:	STYLE 14:
PIN 1. ANODE	PIN 1. DRAIN	PIN 1. ANODE	PIN 1. CATHODE	PIN 1. SOURCE	PIN 1. CATHODE
2. ANODE	2. SOURCE	2. CATHODE	2. CATHODE	2. DRAIN	2. GATE
3. CATHODE	3. GATE	3. CATHODE-ANODE	3. ANODE	3. GATE	3. ANODE
STYLE 15:	STYLE 16:	STYLE 17:	STYLE 18:	STYLE 19:	STYLE 20:
PIN 1. GATE	PIN 1. ANODE	PIN 1. NO CONNECTION	PIN 1. NO CONNECTION	PIN 1. CATHODE	PIN 1. CATHODE
2. CATHODE	2. CATHODE	2. ANODE	2. CATHODE	2. ANODE	2. ANODE
3. ANODE	3. CATHODE	3. CATHODE	3. ANODE	3. CATHODE-ANODE	3. GATE
STYLE 21:	STYLE 22:	STYLE 23:	STYLE 24:	STYLE 25:	STYLE 26:
PIN 1. GATE	PIN 1. RETURN	PIN 1. ANODE	PIN 1. GATE	PIN 1. ANODE	PIN 1. CATHODE
2. SOURCE	2. OUTPUT	2. ANODE	2. DRAIN	2. CATHODE	2. ANODE
3. DRAIN	3. INPUT	3. CATHODE	3. SOURCE	3. GATE	3. NO CONNECTION
STYLE 27: PIN 1. CATHODE 2. CATHODE	STYLE 28: PIN 1. ANODE 2. ANODE				

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3. CATHODE





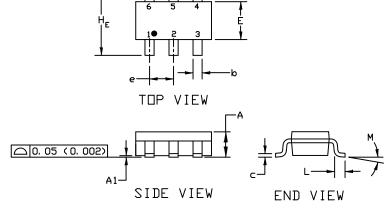
SC-74 CASE 318F ISSUE P

DATE 07 OCT 2021

NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994
- 2. CONTROLLING DIMENSION: INCHES
- MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.

	MILLIMETERS				INCHES	
DIM	MIN.	N□M.	MAX.	MIN.	N□M.	MAX.
A	0. 90	1. 00	1. 10	0. 035	0. 039	0. 043
A1	0. 01	0. 06	0. 10	0. 001	0. 002	0. 004
ھ	0. 25	0. 37	0. 50	0. 010	0. 015	0. 020
С	0.10	0. 18	0. 26	0. 004	0. 007	0. 010
D	2. 90	3. 00	3. 10	0. 114	0. 118	0. 122
Ε	1. 30	1. 50	1. 70	0. 051	0. 059	0. 067
е	0. 85	0. 95	1. 05	0. 034	0. 037	0. 041
Η _E	2. 50	2. 75	3. 00	0. 099	0. 108	0. 118
L	0. 20	0. 40	0. 60	0. 008	0. 016	0. 024
М	0*		10*	0*		10*



GENERIC MARKING DIAGRAM*

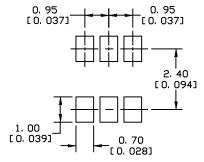


XXX = Specific Device Code

M = Date Code ■ = Pb-Free Package

(Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.



For additional information on our Pb-Free strategy and soldering details, please download the UN Seniconductor Soldering and Mounting Techniques Reference Manual, SULDERRM/D.

SOLDERING FOOTPRINT

STYLE 1: PIN 1. CATHODE 2. ANODE 3. CATHODE 4. CATHODE 5. ANODE 6. CATHODE	STYLE 2: PIN 1. NO CONNECTION 2. COLLECTOR 3. EMITTER 4. NO CONNECTION 5. COLLECTOR 6. BASE	STYLE 3: PIN 1. EMITTER 1 2. BASE 1 3. COLLECTOR 2 4. EMITTER 2 5. BASE 2 6. COLLECTOR 1	STYLE 4: PIN 1. COLLECTOR 2 2. EMITTER 1/EMITTER 2 3. COLLECTOR 1 4. EMITTER 3 5. BASE 1/BASE 2/COLLECTOR 3 6. BASE 3	STYLE 5: PIN 1. CHANNEL 1 2. ANODE 3. CHANNEL 2 4. CHANNEL 3 5. CATHODE 6. CHANNEL 4	STYLE 6: PIN 1. CATHODE 2. ANODE 3. CATHODE 4. CATHODE 5. CATHODE 6. CATHODE
STYLE 7: PIN 1. SOURCE 1 2. GATE 1 3. DRAIN 2 4. SOURCE 2 5. GATE 2 6. DRAIN 1	STYLE 8: PIN 1. EMITTER 1 2. BASE 2 3. COLLECTOR 2 4. EMITTER 2 5. BASE 1 6. COLLECTOR 1	STYLE 9: PIN 1. EMITTER 2 2. BASE 2 3. COLLECTOR 1 4. EMITTER 1 5. BASE 1 6. COLLECTOR 2	STYLE 10: PIN 1. ANODE/CATHODE 2. BASE 3. EMITTER 4. COLLECTOR 5. ANODE 6. CATHODE	STYLE 11: PIN 1. EMITTER 2. BASE 3. ANODE/CATHOD 4. ANODE 5. CATHODE 6. COLLECTOR	E

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